

Gas Cluster Ion Beam Equipment

nFusion™ 500 Series

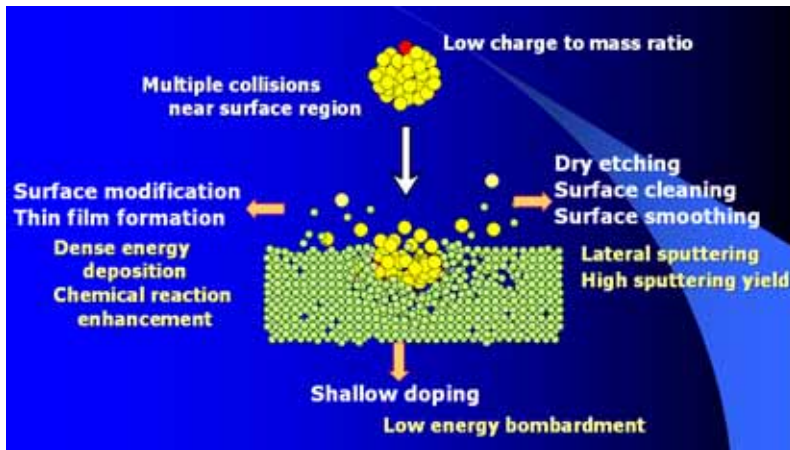
Prof. Isao YAMADA (Kyoto University)



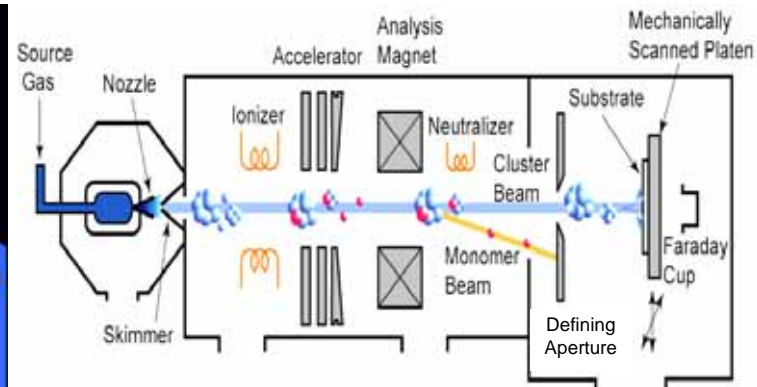
300mm Si Wafer

TEL EPION INC.

Characteristics & Applications of GCIB



GCIB System



Gas Cluster :

$(Ar)_n$, $(O_2)_n$, $(CO_2)_n$,
 $(SF_6)_n$, $(N_2)_n$ ·····
 $n \sim 2000$

- Ultra shallow doping
- Modification of surface structure & composition
- Co-incident doping of multiple species
- Atomic level surface smoothing
- Asperity removal
- Directional etching
- Assisted deposition of thin films

Patent status & Patent owner contact

Patent No. : USP5459326; 5814194; 6207282; 6797334; 6797339

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